

SOT223 PNP SILICON PLANAR MEDIUM POWER HIGH GAIN TRANSISTOR

FZT795A

ISSUE 3 - OCTOBER 1995

FEATURES

- * 140 Volt V_{CEO}
- * Gain of 250 at $I_C=0.2$ Amps and very low $V_{CE(sat)}$

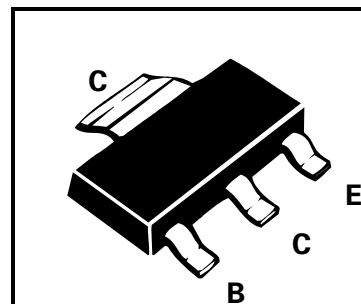
APPLICATIONS

- * Battery powered circuits

COMPLEMENTARY TYPE – FZT694B

PARTMARKING DETAIL – FZT795A

ABSOLUTE MAXIMUM RATINGS.



PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-140	V
Collector-Emitter Voltage	V_{CEO}	-140	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-1	A
Continuous Collector Current	I_C	-500	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	2	W
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$)

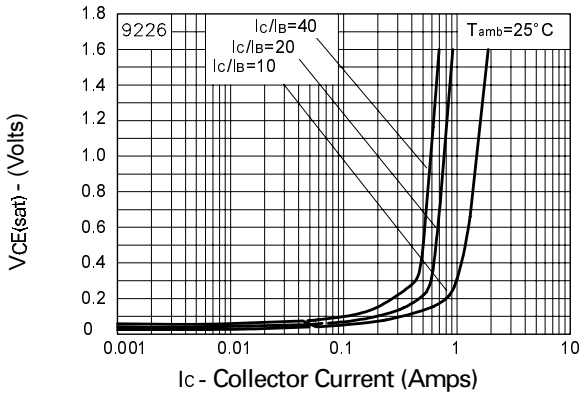
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Breakdown Voltages	$V_{(BR)CBO}$	-140			V	$I_C=-100\mu A$
	$V_{(BR)CEO}$	-140			V	$I_C=-10mA^*$
	$V_{(BR)EBO}$	-5			V	$I_E=-100\mu A$
Cut-Off Currents	I_{CBO}			-0.1	μA	$V_{CB}=-100V$
	I_{EBO}			-0.1	μA	$V_{EB}=-4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.3	V	$I_C=-100mA, I_B=-1mA^*$
				-0.3	V	$I_C=-200mA, I_B=-5mA^*$
				-0.25	V	$I_C=-500mA, I_B=-50mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-0.95	V	$I_C=-500mA, I_B=-50mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.75		V	$I_C=-500mA, V_{CE}=-2V^*$
Static Forward Current Transfer Ratio	h_{FE}	300		800		$I_C=-10mA, V_{CE}=-2V^*$
		250				$I_C=-200mA, V_{CE}=-2V^*$
		100				$I_C=-300mA, V_{CE}=-2V^*$
Transition Frequency	f_T	100			MHz	$I_C=-50mA, V_{CE}=-5V$ $f=50MHz$
Input Capacitance	C_{ibo}		225		pF	$V_{EB}=-0.5V, f=1MHz$
Output Capacitance	C_{obo}		15		pF	$V_{CB}=-10V, f=1MHz$
Switching Times	t_{on}		100		ns	$I_C=-100mA, I_{B1}=-10mA$
	t_{off}		1900		ns	$I_{B2}=-10mA, V_{CC}=-50V$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

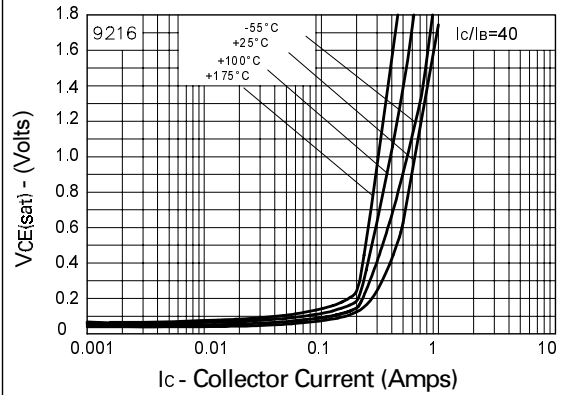
Spice parameter data is available upon request for this device

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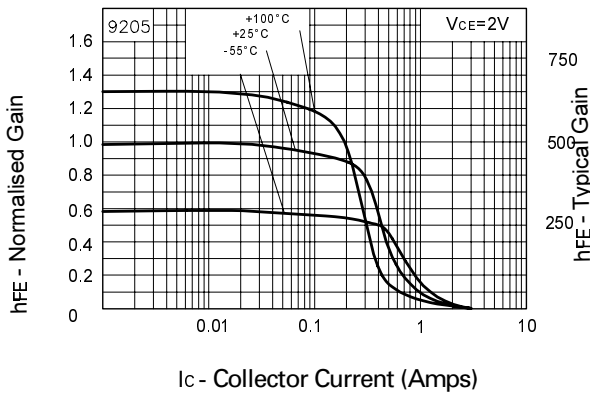
TYPICAL CHARACTERISTICS



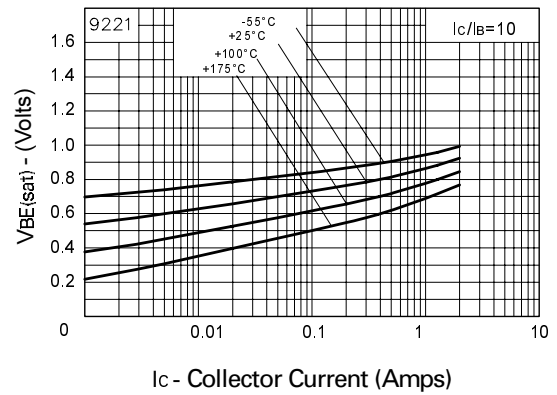
VCE(sat) v IC



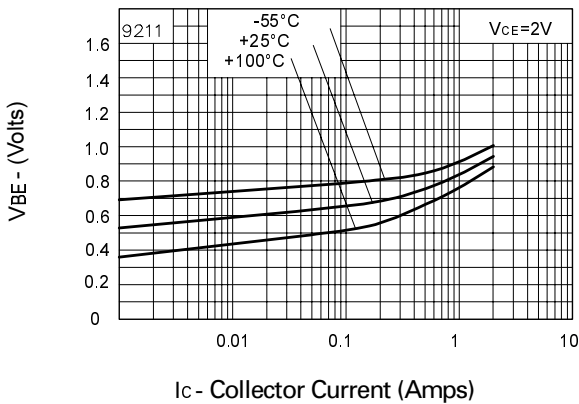
VCE(sat) v IC



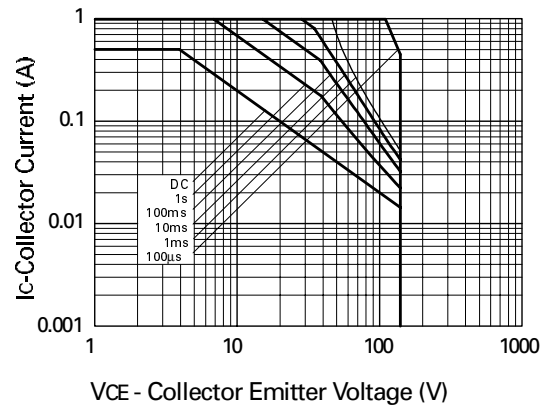
hFE v IC



VBE(sat) v IC



VBE(on) v IC



Safe Operating Area